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PATENT TRADEMARK OFFICE

PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re application of

Jin JANG et al.

Group Art Unit: 2814

Application No.: 09/497,508

Examiner: W. Louie

Filed: February 4, 2000

For: POLYCRYSTALLINE SILICON FILM CONTAINING Ni

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

Dear Sir:

In response to the Examiner's Final Office Action dated January 14, 2002, the following amendments and remarks are respectfully submitted.

IN THE SPECIFICATION:

Page 9, paragraph beginning at line 10:

Referring to Fig. 11C, it is noted that the film is crystallized by crystallites 13 of a needle shape, and the whole amorphous silicon is crystallized uniformly.

Page 9, paragraph beginning at line 14:

Referring to Fig. 11D, needle shaped crystallites are not identified in the drawing, and the whole film is filled with crystallites 14 of a small circle-like shape. Such polysilicon fails to be used for fabricating solar cells, thin film transistors, and the like.

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